NSN 5961-00-458-8681

Thyristor Semiconductor Device - Page 1 of 1

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Inclosure Material:

Metal

Overall Length:

0.450 inches

Overall Diameter:

0.875 inches

Mounting Facility Quantity:

2

Internal Configuration:

Junction contact

Electrode Internally-electrically Connected To Case:

Anode

Mounting Method:

Unthreaded hole

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

50.0 breakover voltage, dc

Current Rating Per Characteristic:

260.00 amperes forward current, average absolute

Power Rating Per Characteristic:

500.0 milliwatts small-signal input power, common-collector blank

Maximum Operating Tempurature Per Measurement Point:

125.0 degrees celsius case

Special Features:

Junction pattern arrangement: pnpn

Terminal Type And Quantity:

2 tab, solder lug and 1 case

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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